



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-92MOD Plastic-Encapsulate Transistors

2SC2482 TRANSISTOR (NPN)

FEATURE

Power dissipation

P_{CM} : 0.9 W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : 0.1 A

Collector-base voltage

$V_{(BR)CBO}$: 300 V

Operating and storage junction temperature range

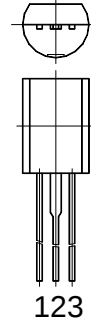
T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

TO-92MOD

1. EMITTER

2. COLLECTOR

3. BASE



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 100\mu A, I_E = 0$	300		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 3\text{ mA}, I_B = 0$	300		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 100\mu A, I_C = 0$	7		V
Collector cut-off current	I_{CBO}	$V_{CB} = 240\text{ V}, I_E = 0$		1	μA
Collector cut-off current	I_{CEO}	$V_{CB} = 220\text{ V}, I_B = 0$		5	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 7\text{ V}, I_C = 0$		1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = 10\text{ V}, I_C = 20\text{ mA}$	30	150	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 10\text{ mA}, I_B = 1\text{ mA}$		1	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = 10\text{ mA}, I_B = 1\text{ mA}$		1	V
Transition frequency	f_T	$V_{CE} = 10\text{ V}, I_C = 20\text{ mA}$ $f = 30\text{ MHz}$	50		MHz

CLASSIFICATION OF $h_{FE(1)}$

Rank	O	Y
Range	30-90	90-150